# **Dual Emitter / Matching Photodetector Series**

Molded Lead Frame and Leadless Ceramic Substrate

The **Dual LED series** consists of a 660nm (red) LED and a companion IR LED such as 880/895, 905, or 940nm. They are widely used for radiometric measurements such as medical analytical and monitoring devices. They can also be used in applications requiring a low cost Bi-Wavelength light source. Two types of pin configurations are available: 1.) three leads with one common anode or cathode, or 2.) two leads parallel back-to-back connection. They are available in two types of packaging. Clear lead frame molded side looker, and leadless ceramic substrate.

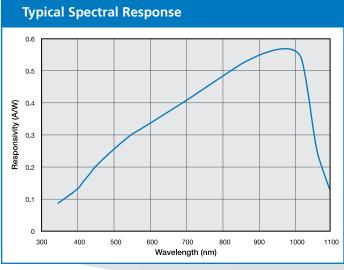
The matching Photodetector' responses are optimized for maximum responsivity at 66nm as well as near IR wavelengths. They exhibit low capacitance and low dark currents and are available in three different active area sizes in the same two types of packaging as the dual emitters: Clear lead frame molded side looker and leadless ceramic substrate.

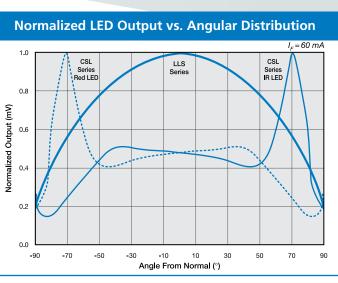
## **APPLICATIONS**

- SpO<sub>2</sub>
- Blood analysis
- Medical Instrumentation
- Ratiometric Instruments

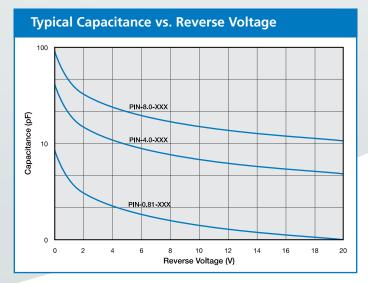
#### **FEATURES**

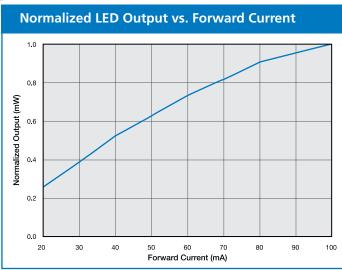
- Leadless ceramic Substrate
- Lead Frame Molded Packages
- Two and Three Lead Designs
- Bi-Wavelengths LEDs
- Matching Detector Response











# **Dual Emitter / Matching Photodetector Series**Molded Lead Frame and Leadless Ceramic Substrate

nber	Active Area			Capaci- tance Dark Current (nA)	Max. Reverse Voltage	Operating Temp.	Storage Temp.				
Model Number		su	nm	A/W		pF	-10 V	V			Package
	Area mn	Dimensio		660nm	900nm	-10 V	typ.	10μΑ	°C	°C	
Photodiode Characteristics «											
PIN-0.81-LLS	0.81	04 4 02 :					2				62 /Leadless Ceramic
PIN-0.81-CSL		1.02 φ				2.0					60 / Molded Lead Frame

PIN	N-0.81-LLS	0.81	1.02.4				2.0	2				Ceramic
PIN	N-0.81-CSL	0.61	1.02 φ				2.0	2				60 / Molded Lead Frame
PI	N-4.0-LLS	3.9	2.31 x 1.68	350 - 1100	0.33	0.55	10	5	20	-25 ~ +85	-40 ~ +100C	62 /Leadless Ceramic
PI	N-4.0-CSL	3.9										60 / Molded Lead Frame
PI	N-8.0-LLS	0.4	8.4 2.9 Sa.				25	10				62 /Leadless Ceramic
PI	N-8.0-CSL	0.4	2.9 Sq.				25	10				60 / Molded Lead Frame

For mechanical drawings and pin locations, please refer to pages 61 to 77.  $^{\rm \tiny o}$  Minimum order quantities apply

Model Number	LED's Used		Package Style ¶	Pin Configuration	Operating Temperature	Storage Temperature
Σ					°c	
<b>Dual Emitter Combination</b>	ıs «					
DLED-660/880-LLS-2		880	64 / Leadless Ceramic	2 Leads / Back to Back*	-25 ~ +85	-40 ~ +80
DLED-660/895-LLS-2		895				
DLED-660/905-LLS-2		905				
DLED-660/905-LLS-3		905		21d-/C Ad-		
DLED-660/940-LLS-3		940		3 Leads / Common Anode		
DLED-660/880-CSL-2	660	880				
DLED-660/895-CSL-2 DLED-660/905-CSL-2 DLED-660/905-CSL-3 DLED-660/940-CSL-3		895		2 Leads / Back to Back*	-5	4
		905	63 / Side Looker Plastic			
		905		21 1 /6 1		
		940		3 Leads / Common Anode		

<sup>\*</sup> In Back-to-Back configuration, the LED's are connected in parallel.

<sup>«</sup> Minimum order quantities apply

	Peak Wavelength	Radiant Flux	Spectral Bandwidth	Forward Voltage	Reverse Voltage V	
	nm	nW	nm	v		
LED	i <sub>f</sub> =20mA	i <sub>f</sub> =20mA	i <sub>f</sub> =20mA FWHN	i <sub>f</sub> =20mA	i <sub>f</sub> =20mA	
	typ.	typ.	typ.	max.	max.	

## **LED Characteristics**

660nm	660	1.8	25	2.4	
880nm	880	1.5	80	2.0	
895nm	895	2.0	50	1.7	5
905nm	905	2.0			
935nm	935	1.5		1.5	
940nm	940	1.5		1.5	

For mechanical drawings, please refer to pages 61 thru 73.

# **Photodiode Care and Handling Instructions**

#### **AVOID DIRECT LIGHT**

Since the spectral response of silicon photodiode includes the visible light region, care must be taken to avoid photodiode exposure to high ambient light levels, particularly from tungsten sources or sunlight. During shipment from OSI Optoelectronics, your photodiodes are packaged in opaque, padded containers to avoid ambient light exposure and damage due to shock from dropping or jarring.

#### **AVOID SHARP PHYSICAL SHOCK**

Photodiodes can be rendered inoperable if dropped or sharply jarred. The wire bonds are delicate and can become separated from the photodiode's bonding pads when the detector is dropped or otherwise receives a sharp physical blow.

#### CLEAN WINDOWS WITH OPTICAL GRADE CLOTH / TISSUE

Most windows on OSI Optoelectronics photodiodes are either silicon or quartz. They should be cleaned with isopropyl alcohol and a soft (optical grade) pad.

#### **OBSERVE STORAGE TEMPERATURES AND HUMIDITY LEVELS**

Photodiode exposure to extreme high or low storage temperatures can affect the subsequent performance of a silicon photodiode. Storage temperature guidelines are presented in the photodiode performance specifications of this catalog. Please maintain a non-condensing environment for optimum performance and lifetime.

#### **OBSERVE ELECTROSTATIC DISCHARGE (ESD) PRECAUTIONS**

OSI Optoelectronics photodiodes, especially with IC devices (e.g. Photops) are considered ESD sensitive. The photodiodes are shipped in ESD protective packaging. When unpacking and using these products, anti-ESD precautions should be observed.

#### DO NOT EXPOSE PHOTODIODES TO HARSH CHEMICALS

Photodiode packages and/or operation may be impaired if exposed to CHLOROTHENE, THINNER, ACETONE, or TRICHLOROETHYLENE.

#### **INSTALL WITH CARE**

Most photodiodes in this catalog are provided with wire or pin leads for installation in circuit boards or sockets. Observe the soldering temperatures and conditions specified below:

Soldering Iron: Soldering 30 W or less

Temperature at tip of iron 300°C or lower.

Dip Soldering: Bath Temperature: 260±5°C.

Immersion Time: within 5 Sec. Soldering Time: within 3 Sec.

Vapor Phase Soldering: DO NOT USE

Reflow Soldering: DO NOT USE

Photodiodes in plastic packages should be given special care. Clear plastic packages are more sensitive to environmental stress than those of black plastic. Storing devices in high humidity can present problems when soldering. Since the rapid heating during soldering stresses the wire bonds and can cause wire to bonding pad separation, it is recommended that devices in plastic packages to be baked for 24 hours at 85°C.

The leads on the photodiode **SHOULD NOT BE FORMED**. If your application requires lead spacing modification, please contact OSI Optoelectronics Applications group at (310)978-0516 before forming a product's leads. Product warranties could be voided.



\*Most of our standard catalog products are RoHS Compliant. Please contact us for details

### 1. Parameter Definitions:

- A = Distance from top of chip to top of glass.
- a = Photodiode Anode.
- B = Distance from top of glass to bottom of case.
- c = Photodiode Cathode
  - (Note: cathode is common to case in metal package products unless otherwise noted).
- W = Window Diameter.
- F.O.V. = Filed of View (see definition below).
- 2. Dimensions are in inches (1 inch = 25.4 mm).
- 3. Pin diameters are  $0.018 \pm 0.002$ " unless otherwise specified.
- 4. Tolerances (unless otherwise noted)

General: 0.XX ±0.01"

0.XXX ±0.005"

Chip Centering: ±0.010" Dimension 'A': ±0.015"

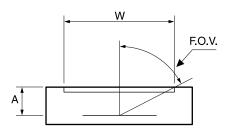
#### 5. Windows

All 'UV' Enhanced products are provided with QUARTZ glass windows,  $0.027 \pm 0.002$ " thick.

All 'XUV' products are provided with removable windows.

All 'DLS' PSD products are provided with A/R coated glass windows.

All 'FIL' photoconductive and photovoltaic products are epoxy filled instead of glass windows.



$$F.O.V. = \tan^{-1}\left(\frac{W}{2A}\right)$$



For Further Assistance Please Call One of Our Experienced Sales and Applications Engineers

310-978-0516

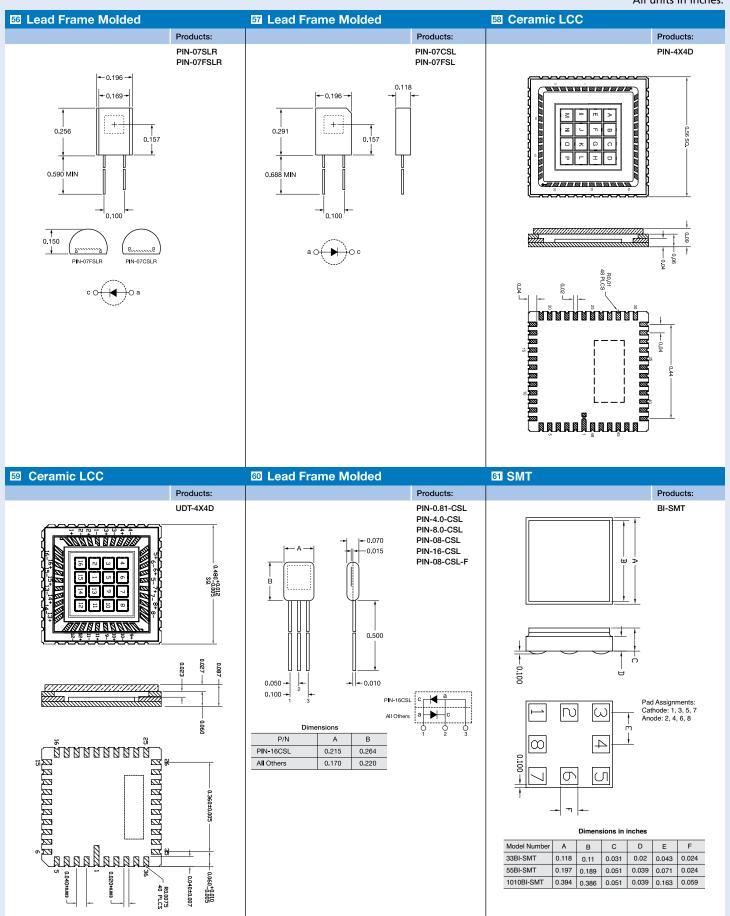
OSI Optoelectronics
An OSI Systems Company



- Or visit our website at
www.osioptoelectronics.com

## **Mechanical Specifications**

All units in inches.



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All units in inches.

